

N-channel TrenchMOS standard level FET Rev. 03 — 7 April 2010

Product data sheet

Product profile 1.

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using NXP High-Performance Automotive (HPA) TrenchMOS technology. This product has been designed and qualified to the appropriate AEC standard for use in automotive critical applications.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Q101 compliant

- Suitable for standard level gate drive sources
- Suitable for thermally demanding environments due to 175 °C rating

1.3 Applications

- 12 V Loads
- Automotive systems

- General purpose power switch
- Motors, lamps and solenoids

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; see <u>Figure 1</u> ; see <u>Figure 4</u>	<u>[1]</u>	-	-	75	A
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	105	W
Static cha	racteristics						
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A};$ $T_j = 25 \text{ °C}; \text{ see } Figure 12;$ see Figure 13		-	5	7	mΩ
Avalanche	e ruggedness						
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$ \begin{split} I_D &= 75 \text{ A}; \text{V}_{sup} \leq 30 \text{V}; \\ R_{GS} &= 50 \Omega; \text{V}_{GS} = 10 \text{V}; \\ T_{j(\text{init})} &= 25 ^\circ\text{C}; \text{ unclamped} \end{split} $		-	-	198	mJ
Dynamic o	characteristics						
Q_{GD}	gate-drain charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V};$ $V_{GS} = 10 \text{ V}; \text{ see } Figure 14$		-	10.7	-	nC

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[1] Continuous current is limited by package.

2. Pinning information

Table 2.	Pinning information				
Pin	Symbol	Description	Simplified outline	Graphic symbol	
1	S	source		_	
2	S	source	mb		
3	S	source			
4	G	gate			
mb	D	mounting base; connected to drain	$ \begin{array}{cccccccccccccccccccccccccccccccccccc$	mbb076 S	
			SOT669 (LFPAK)		

3. Ordering information

Table 3. Ordering in	formation		
Type number	Package		
	Name	Description	Version
BUK7Y07-30B	LFPAK	plastic single-ended surface-mounted package (LFPAK); 4 leads	SOT669

4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

					_		
Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	30	V
V _{DGR}	drain-gate voltage	$R_{GS} = 20 \text{ k}\Omega$		-	-	30	V
V _{GS}	gate-source voltage			-20	-	20	V
I _D	drain current	$T_{mb} = 25 \text{ °C}; V_{GS} = 10 \text{ V}; \text{ see } Figure 1;$ see Figure 4	<u>[1]</u>	-	-	75	А
		T_{mb} = 100 °C; V_{GS} = 10 V; see Figure 1		-	-	63	А
I _{DM}	peak drain current	T_{mb} = 25 °C; $t_p \le 10 \ \mu$ s; pulsed; see <u>Figure 4</u>		-	-	356	А
P _{tot}	total power dissipation	T _{mb} = 25 °C; see <u>Figure 2</u>		-	-	105	W
T _{stg}	storage temperature			-55	-	175	°C
Tj	junction temperature			-55	-	175	°C
Source-drai	n diode						
I _S	source current	T _{mb} = 25 °C	<u>[1]</u>	-	-	75	А
I _{SM}	peak source current	$t_p \le 10 \ \mu s$; pulsed; $T_{mb} = 25 \ ^{\circ}C$		-	-	356	А
Avalanche r	ruggedness						
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	$\label{eq:ld} \begin{array}{l} I_D = 75 \text{ A}; \ V_{sup} \leq 30 \text{ V}; \ R_{GS} = 50 \ \Omega; \\ V_{GS} = 10 \text{ V}; \ T_{j(init)} = 25 \ ^\circ\text{C}; \ unclamped \end{array}$		-	-	198	mJ
E _{DS(AL)R}	repetitive drain-source avalanche energy	see Figure 3	[2][3][4] [5]	-	-	-	J

[1] Continuous current is limited by package.

[2] Single-pulse avalanche rating limited by maximum junction temperature of 175 °C.

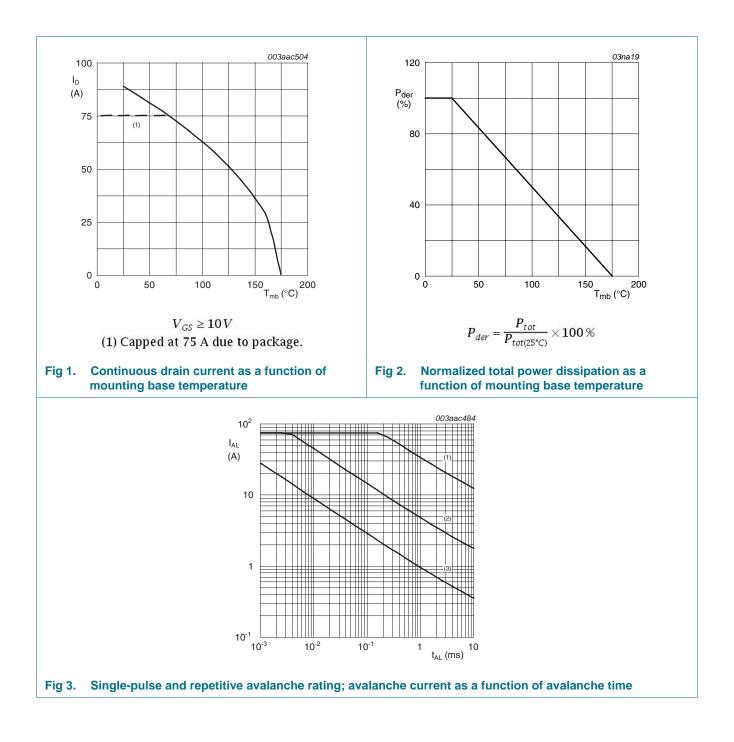
[3] Repetitive avalanche rating limited by an average junction temperature of 170 °C.

[4] Refer to application note AN10273 for further information.

[5] Maximum value not quoted. Repetitive rating defined in avalanche rating figure.

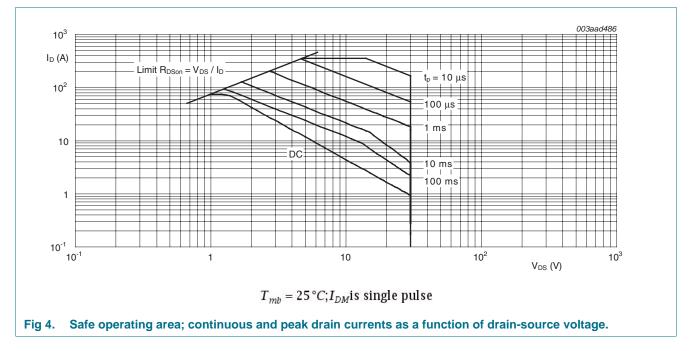
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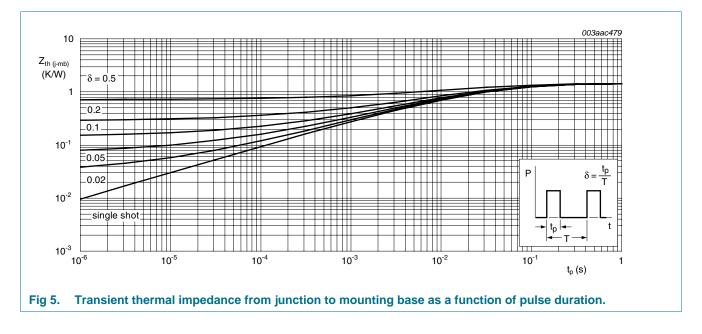
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5. Thermal characteristics

Table 5.Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	see <u>Figure 5</u>	-	-	1.42	K/W

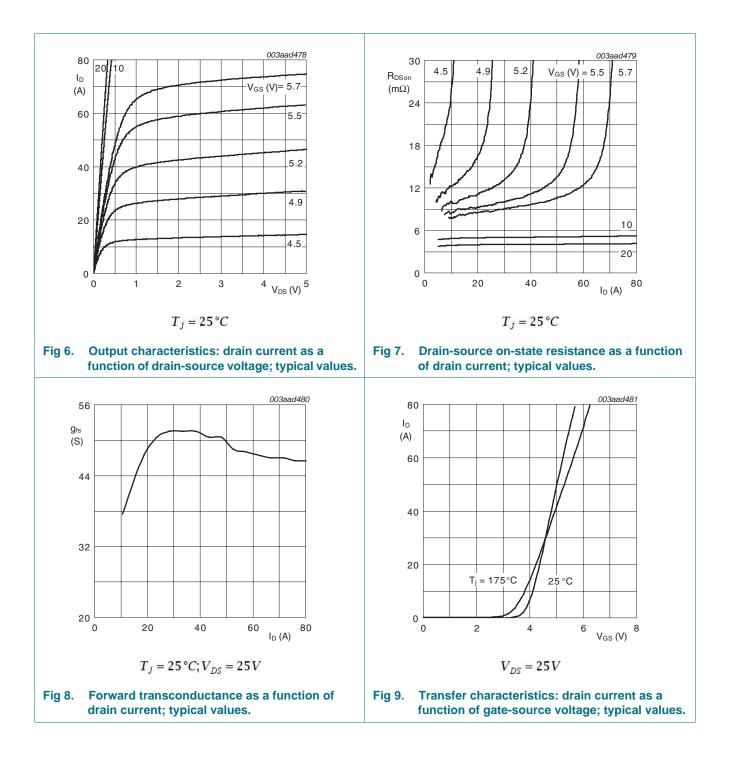


6. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		Conditions	IVIIII	тур	Wax	Unit
	aracteristics		00			
V _{(BR)DSS}	drain-source breakdown voltage	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = 25 \ ^{\circ}\text{C}$	30	-	-	V
	<u> </u>	$I_D = 250 \ \mu\text{A}; \ V_{GS} = 0 \ V; \ T_j = -55 \ ^\circ\text{C}$	27	-	-	V
V _{GS(th)}	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ °C};$ see <u>Figure 10</u> ; see <u>Figure 11</u>	2	3	4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = -55 °C; see <u>Figure 10</u>	-	-	4.4	V
		I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 175 °C; see <u>Figure 10</u>	1	-	-	V
I _{DSS}	drain leakage current	V _{DS} = 30 V; V _{GS} = 0 V; T _j = 25 °C	-	0.02	1	μA
		V _{DS} = 30 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	$V_{DS} = 0 \text{ V}; \text{ V}_{GS} = 20 \text{ V}; \text{ T}_{j} = 25 \text{ °C}$	-	2	100	nA
		V _{DS} = 0 V; V _{GS} = -20 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 175 \text{ °C};$ see Figure 12; see Figure 13	-	-	13.4	mΩ
		$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 \text{ °C};$ see Figure 12; see Figure 13	-	5	7	mΩ
Dynamic	characteristics					
Q _{G(tot)}	total gate charge	$I_D = 25 \text{ A}; V_{DS} = 24 \text{ V}; V_{GS} = 10 \text{ V};$	-	31	-	nC
Q _{GS}	gate-source charge	see Figure 14	-	9.5	-	nC
Q _{GD}	gate-drain charge		-	10.7	-	nC
C _{iss}	input capacitance	V _{GS} = 0 V; V _{DS} = 25 V; f = 1 MHz;	-	1330	1773	pF
C _{oss}	output capacitance	T _j = 25 °C; see <u>Figure 15</u>	-	495	594	pF
C _{rss}	reverse transfer capacitance		-	206	282	pF
t _{d(on)}	turn-on delay time	$V_{DS} = 25 \text{ V}; \text{ R}_{L} = 1 \Omega; \text{ V}_{GS} = 10 \text{ V};$	-	17	-	ns
t _r	rise time	$R_{G(ext)} = 10 \Omega$	-	30	-	ns
t _{d(off)}	turn-off delay time		-	40	-	ns
t _f	fall time		-	28	-	ns
Source-d	rain diode					
V _{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ °C};$ see <u>Figure 16</u>	-	0.85	1.2	V
t _{rr}	reverse recovery time	$I_{S} = 20 \text{ A}; \text{ dI}_{S}/\text{dt} = -100 \text{ A}/\mu\text{s}; \text{ V}_{GS} = 0 \text{ V};$	-	39	-	ns
Q _r	recovered charge	V _{DS} = 25 V	-	53	-	nC

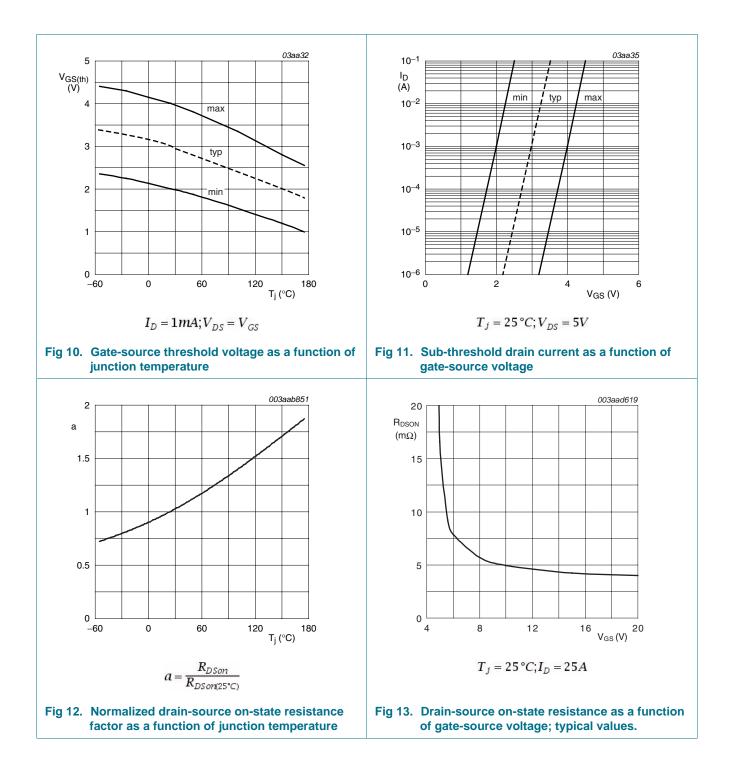
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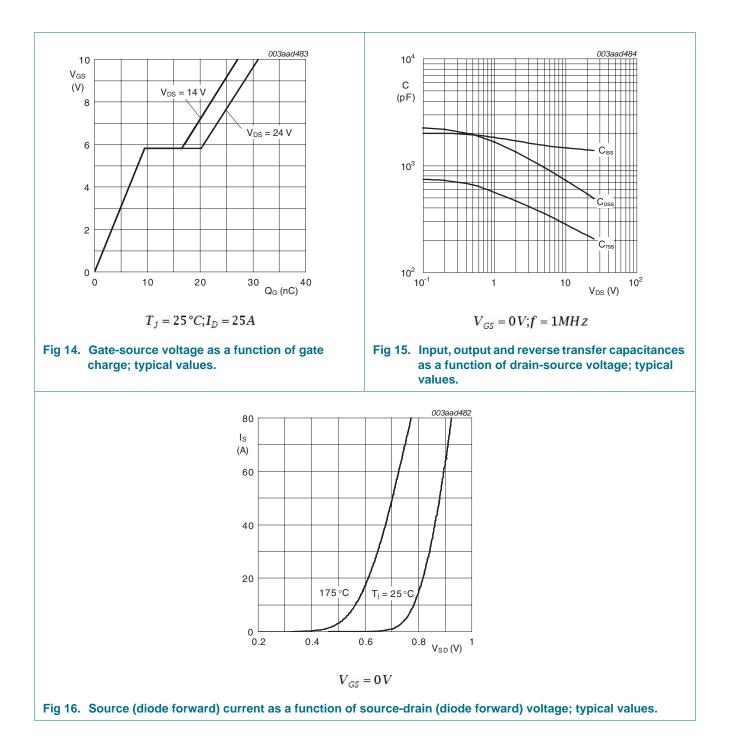
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7. Package outline

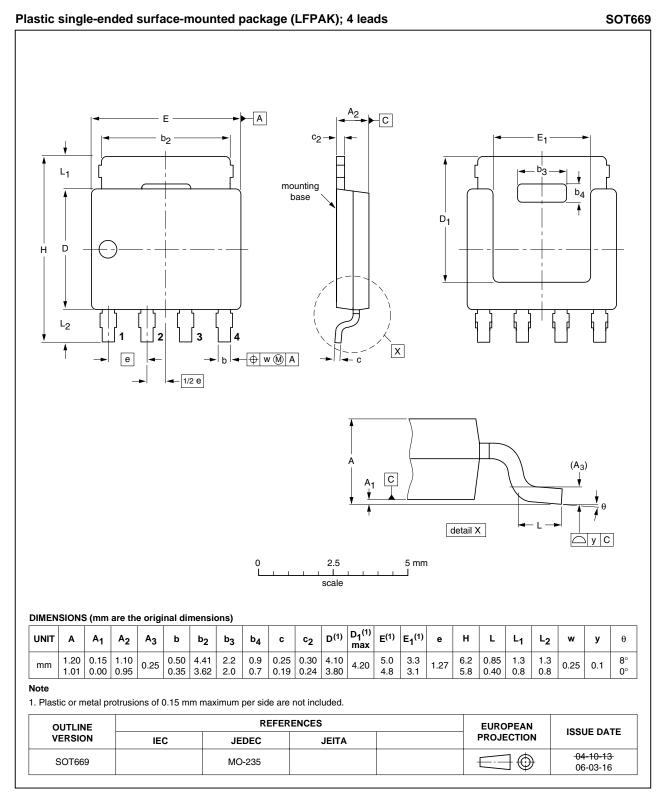


Fig 17. Package outline SOT669 (LFPAK)

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8. Revision history

Table 7. Revision his	story			
Document ID	Release date	Data sheet status	Change notice	Supersedes
BUK7Y07-30B_3	20100407	Product data sheet	-	BUK7Y07-30B_2
Modifications:	 Status char 	nged from objective to pro	duct.	
BUK7Y07-30B_2	20100215	Objective data sheet	-	BUK7Y07-30B_1

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9. Legal information

9.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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